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# P-Channel 40 V (D-S) MOSFET

#### **DESCRIPTION**

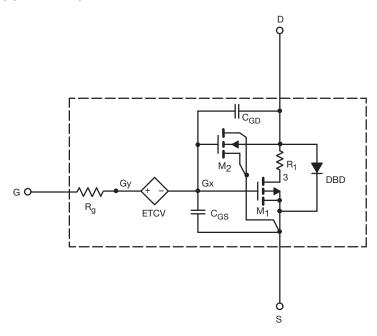
The attached SPICE model describes the typical electrical characteristics of the P-Channel vertical DMOS. The subcircuit model is extracted and optimized over the -55 °C to +150 °C temperature ranges under the pulsed -20 V to +20 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched  $C_{\rm gd}$  model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

#### **CHARACTERISTICS**

- P-channel vertical DMOS
- Macro model (subcircuit model)
- Level 3 MOS
- · Apply for both linear and switching application
- Accurate over the -55 °C to +150 °C temperature range
- Model the gate charge

#### SUBCIRCUIT MODEL SCHEMATIC



#### Note

• This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits



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<b>SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	TEST CONDITIONS	SIMULATED DATA	MEASURED DATA	UNIT
Static					
Gate-source threshold voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = -250 \mu A$	-1.9	-	V
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = -10 \text{ V}, I_D = -20 \text{ A}$	0.001725	0.0018	Ω
		$V_{GS} = -4.5 \text{ V}, I_D = -20 \text{ A}$	0.00225	0.0023	
Forward transconductance a	9fs	$V_{DS} = -15 \text{ V}, I_D = -20 \text{ A}$	161	125	S
Body diode voltage	$V_{SD}$	$I_F = -10 \text{ A}, V_{GS} = 0 \text{ V}$	0.72	0.75	V
Dynamic <sup>b</sup>					
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -15 V, V <sub>GS</sub> = 0 V, f = 1 MHz	21650	21850	pF
Output capacitance	C <sub>oss</sub>		1658	1500	
Reverse transfer capacitance	C <sub>rss</sub>		1448	1320	
Total gate charge	Qg	$V_{DS} = -15 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -20 \text{ A}$	392	392	nC
		$V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -20 \text{ A}$	197	180	
Gate-source charge	Q <sub>gs</sub>		67	65	
Gate-drain charge	Q <sub>gd</sub>		53	59	

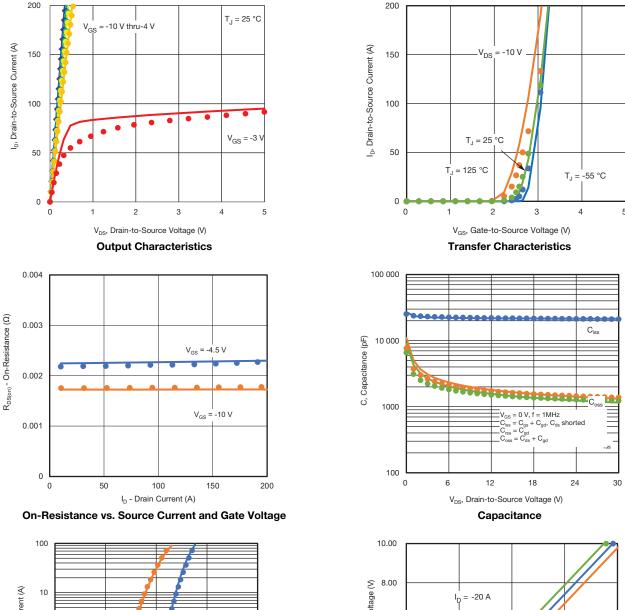
#### **Notes**

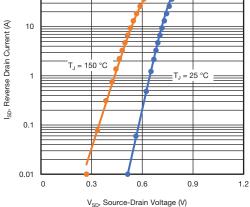
- a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing

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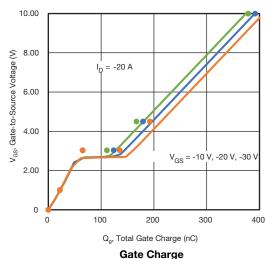
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### **COMPARISON OF MODEL WITH MEASURED DATA** ( $T_J = 25$ °C, unless otherwise noted)





Source-Drain Diode Forward Voltage



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